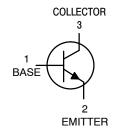


General Purpose Transistors

NPN Silicon

BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L





SOT-23 CASE 318 STYLE 6

Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	٧
Collector - Base Voltage	V_{CBO}	50	V
Emitter – Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

MARKING DIAGRAM



6x = Device Codex = A, B, or C

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	45	-	-	V
Collector – Emitter Breakdown Voltage (V _{EB} = 0, I _C = 10 μA)	V _{(BR)CES}	50	-	-	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	5.0	-	-	V
Collector Cutoff Current $(V_{CB} = 20 \text{ V})$ $(V_{CB} = 20 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}		_ _	100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{c} (I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}) \\ & BC817-16, SBC817-16 \\ & BC817-25, SBC817-25 \\ & BC817-40, SBC817-40 \\ \end{array} $ $ (I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}) $	h _{FE}	100 160 250 40	- - -	250 400 600	-
Collector – Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	-	-	0.7	V
Base – Emitter On Voltage (I _C = 500 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	-	1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]		
BC817-16LT1G			0000 / Tana 9 Dayl		
NSVBC817-16LT1G		SOT-23	3000 / Tape & Reel		
BC817-16LT3G	6A	(Pb-Free)	10,000 / Tape & Reel		
SBC817-16LT3G		10,000 /			
BC817-25LT1G			0000 /Taba & Basil		
SBC817-25LT1G	2.0	SOT-23 (Pb-Free)	3000 / Tape & Reel		
BC817-25LT3G	6B		40.000 /Taba 0 Bad		
SBC817-25LT3G			10,000 / Tape & Reel		
BC817-40LT1G			0000 / Tana 9 Davi		
SBC817-40LT1G		SOT-23	3000 / Tape & Reel		
BC817-40LT3G	6C	(Pb-Free)	40.000 /Taba 0 Bask		
SBC817-40LT3G			10,000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L

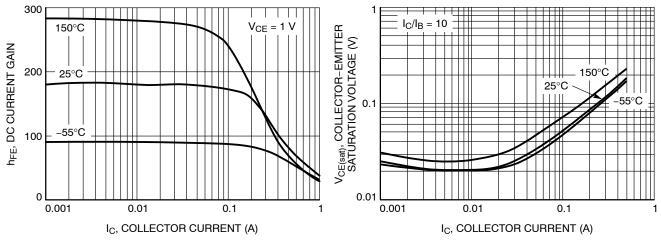


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

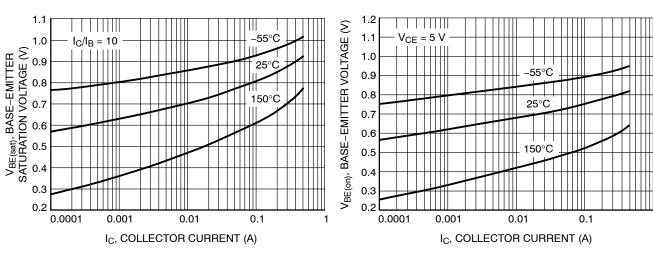


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Voltage vs. Collector Current

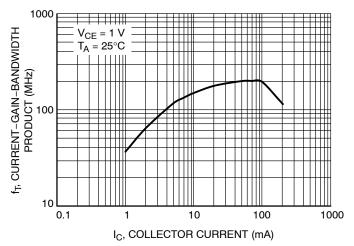
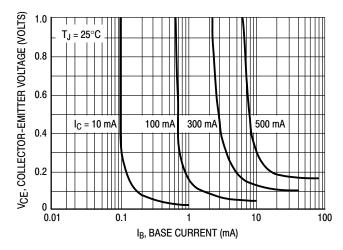


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L



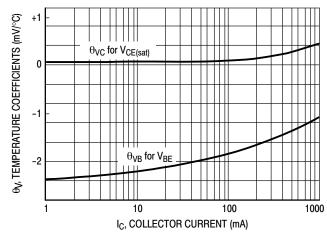


Figure 6. Saturation Region

Figure 7. Temperature Coefficients

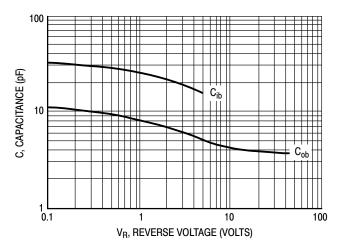


Figure 8. Capacitances

TYPICAL CHARACTERISTICS - BC817-25L, SBC817-25L

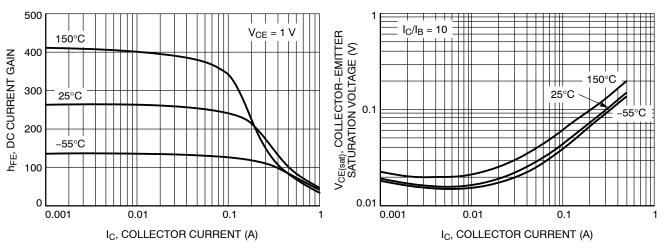


Figure 9. DC Current Gain vs. Collector Current

Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

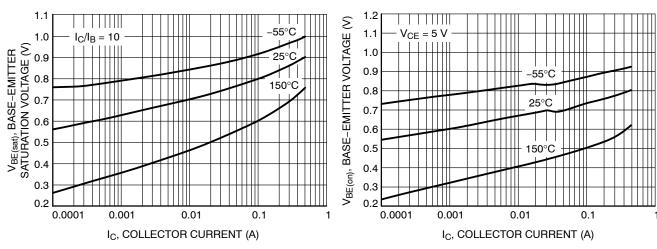


Figure 11. Base Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Voltage vs. Collector Current

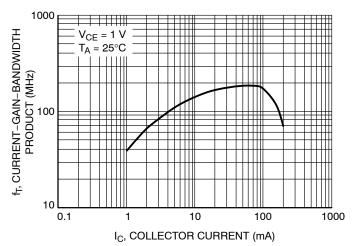
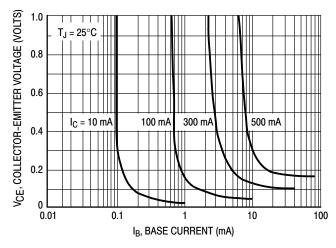


Figure 13. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-25L, SBC81725L



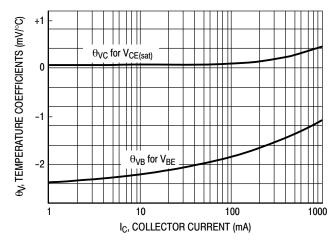


Figure 14. Saturation Region

Figure 15. Temperature Coefficients

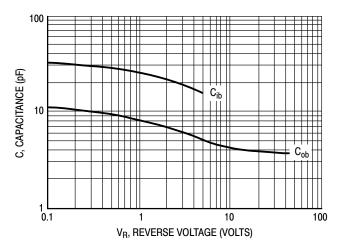


Figure 16. Capacitances

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L

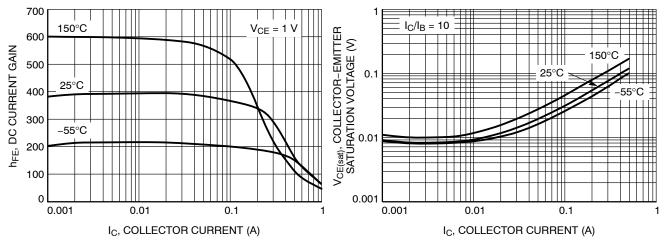


Figure 17. DC Current Gain vs. Collector Current

Figure 18. Collector Emitter Saturation Voltage vs. Collector Current

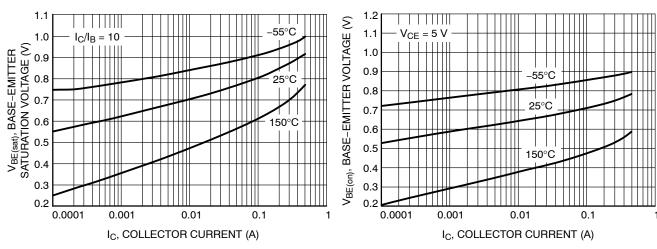


Figure 19. Base Emitter Saturation Voltage vs. Collector Current

Figure 20. Base Emitter Voltage vs. Collector Current

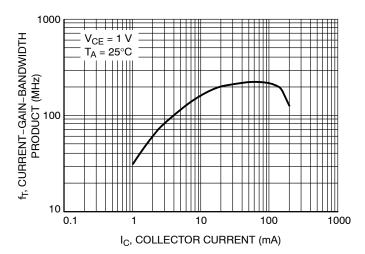
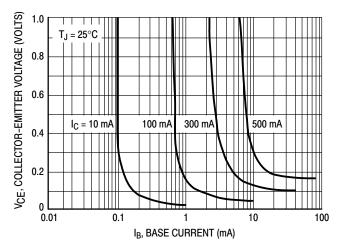


Figure 21. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L



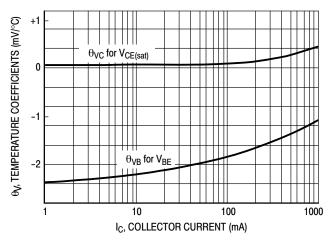


Figure 22. Saturation Region

Figure 23. Temperature Coefficients

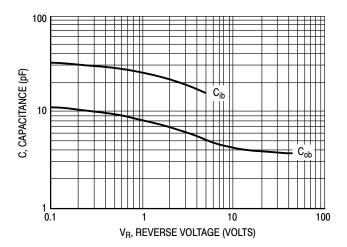


Figure 24. Capacitances

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

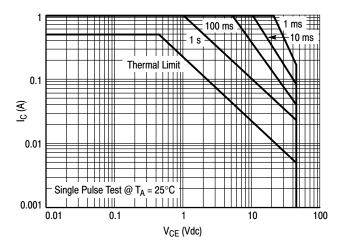


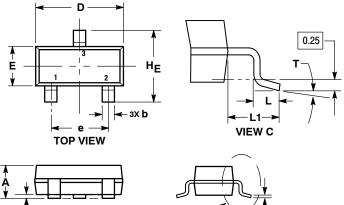
Figure 25. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1



SEE VIEW C

END VIEW

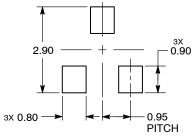
NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	M	ILLIMETE	RS		INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	0.89 1.00 1.11 0.01 0.06 0.10 0.37 0.44 0.50		0.035	0.039	0.044
A1	0.01			0.000	0.002	0.004
b	0.37			0.015	0.017	0.020
С			0.20	0.003	0.006	0.008
D			3.04	0.110	0.114	0.120
E	1.20	.20 1.30 1.40		0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L			0.55	0.012	0.017	0.022
L1			0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

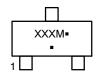
RECOMMENDED SOLDERING FOOTPRINT

SIDE VIEW



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
STVI F a	OTV/1 F 40:	OT/1 E 44	OT (1 5 40)

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	GATE	CATHODE-ANODE	ANODE	GATE	ANODE

STYLE 1	5:	STYLE 1	6:	STYLE 1	7:	STYLE 1	8:	STYLE 1	19:	STYLE 2	20:
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	NO CONNECTION	PIN 1.	NO CONNECTION	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	CATHODE	2.	CATHODE	2.	ANODE	2.	CATHODE	2.	ANODE	2.	ANODE
3.	ANODE	3.	CATHODE	3.	CATHODE	3.	ANODE	3.	CATHODE-ANODE	3.	GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPUT	3 CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION

2. CATHODE 2.	28: . ANODE 2. ANODE 3. ANODE	
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PAGE 1 OF 1

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